Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S18 4	17	photovolt\$5 near10 device and (sige or silicon near2 germanium) near10 thickness near10 nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/06 10:00
S18 3	9552	photovolt\$5 near10 device	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/06 10:00
S18 2	0	("6118151" or "5753541").pn. and photovolt\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/06 10:00
S18 5	18	photovolt\$5 near10 device and (sige or silicon near2 germanium) near10 thick\$6 near10 nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/06 10:03
S18 8	58	photovolt\$6 near10 (thin near2 film near2 transistor or tft) and (sige or silicon near2 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/06 10:05
S18 7	313	photovolt\$6 near10 (thin near2 film near2 transistor or tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/06 10:05
S18 6	18	yamazaki near2 shunpei.in. and laminat\$6 near10 total near5 thick\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/06 10:05
S18 9	18	photovoltaic near10 device and (sige or silicon near2 germanium) near10 thick\$6 near10 nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:40
S19 3	0	photovoltaic near10 device and noguchi near2 shigeru.in. and thick\$6 near16 sige	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:41

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S19 2	19	photovoltaic near10 device and noguchi near2 shigeru.in. and thick\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:41
S19 1	48	photovoltaic near10 device and noguchi near2 shigeru.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:41
S19 0	268	photovoltaic near10 device and (sige or silicon near2 germanium) and thick\$6 near10 nm	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:41
S19 4	2	photovoltaic near10 device and noguchi near2 shigeru.in. and sige	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:42
S19 5	1	photovoltaic near10 device and noguchi near2 shigeru.in. and sige and thick\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:44
S19 7	0	multibandgap near2 photovoltaic near10 device and (sige or silicon near2 germanium) near16 thick\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:47
S20 1	2	band\$1gap near2 photovoltaic near10 device and (sige or silicon near2 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:48
S20 0	0	multiple near2 band\$1gap near2 photovoltaic near10 device and (sige or silicon near2 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:48
S19 9	0	multiple near2 bandgap near2 photovoltaic near10 device and (sige or silicon near2 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:48
S19 8	0	multibandgap near2 photovoltaic near10 device and (sige or silicon near2 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:48

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S19 6	127	photovoltaic near10 device and (sige or silicon near2 germanium) near16 thick\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:50
S20 4	260	(photovoltaic near10 device or solar near2 cell) and (sige or silicon near2 germanium) near16 thick\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:51
S20 3	1	(photovoltaic near10 device or solar near2 cell) and (sige or silicon near2 germanium) near16 thick\$6 and 117/1-5.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:51
\$20 2	0	photovoltaic near10 device and (sige or silicon near2 germanium) near16 thick\$6 and 117/1-5.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:51
S20 5	128	(photovoltaic near10 device or solar near2 cell) and (sige or silicon near2 germanium) near16 thick\$6 and @py<"2001"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:52
S20 6	2	(photovoltaic near10 device or solar near2 cell) and polycrystal\$7 near6 (sige or silicon near2 germanium) near16 thick\$6 and @py<"2001"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:55
S20 7	6	multi\$1bandgap near5 photovolt\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:56
S20 9	994	shunpei near2 yamazaki.in. and film near5 thick\$6 near10 nm and (silicon near4 germanium or sige)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:58
S20 8	12	(solar or photovolt\$6) and (sige or silicon near2 germanium) near10 thick\$6 near10 polycrystal\$7	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:58
S21 0	483	shunpei near2 yamazaki.in. and film near5 thick\$6 near10 nm same (silicon near4 germanium or sige)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 11:59

S21 1	88	shunpei near2 yamazaki.in. and film near5 thick\$6 near10 nm near15 (silicon near4 germanium or sige)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 17:36
L3	16	2 and (sige or silicon near2 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 17:56
L2	33	US-5932893-\$.DID. OR US-5943560-\$. DID. OR US-5977560-\$.DID. OR US-6087679-\$.DID. OR US-6107654-\$. DID. OR US-6307214-\$.DID. OR US-6307220-\$.DID. OR US-6335541-\$. DID. OR US-6346716-\$.DID. OR US-6452211-\$.DID. OR US-6495886-\$. DID. OR US-6690068-\$.DID. OR US-6693044-\$. DID. OR US-6787807-\$.DID. OR US-6828587-\$.DID. OR US-6956235-\$. DID.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 17:56
L1	3	"6482684".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 17:56
L4	5	2 and (sige or silicon near2 germanium) near10 amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 17:57
S18 1	491	((shunpei near2 yamazaki or toru near2 mitsuki or kenji near2 kasahara or tamae near2 takano or takeshi near2 shichi or chiho near2 kokubo). in. or semiconductor near2 energy near2 laboratory.as.) and laser near16 (crystal\$6 anneal\$6 or recrystal\$6) same (sige or silicon near2 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 18:00
L5	0	((shunpei near2 yamazaki or toru near2 mitsuki or kenji near2 kasahara or tamae near2 takano or takeshi near2 shichi or chiho near2 kokubo). in. or semiconductor near2 energy near2 laboratory.as.) and laser near16 (crystal\$6 anneal\$6 or recrystal\$6) same (sige or silicon near2 germanium) near10 thick\$6	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/15 18:00